



Docket No. 740756-2063

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Patent Application of:

Shunpei YAMAZAKI et al.

Serial No. 09/436,984

Filed: November 9, 1999

For: SEMICONDUCTOR DEVICE AND
MANUFACTURING METHOD THEREOF

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Group Art Unit: 2823

Examiner: William D. Coleman

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on 12-2-2002

Adile M. Stamp

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed July 31, 2002, please amend the above identified application as follows.

IN THE SPECIFICATION:

At page 1, line 1, please replace the title with a new title as follows:

-- SEMICONDUCTOR DEVICE HAVING AN IMPURITY GRADIENT IN
THE IMPURITY REGIONS AND METHOD OF MANUFACTURE--

IN THE CLAIMS:

Please add the following new claims 56-59:

56. (New) The semiconductor device according to claim 32, wherein the pair of side walls overlap only the pair of first impurity regions.

57. (New) The semiconductor device according to claim 38, wherein the pair of side walls overlap only the pair of first impurity regions.

58. (New) The semiconductor device according to claim 44, wherein the pair of side walls overlap only the pair of first impurity regions.